

Appl. No. : 10/719,277
Filed : November 20, 2003

7. (Original) The method of Claim 1, wherein the sacrificial material completely fills the open volume before being selectively removed.

8. (Canceled).

9. (Currently Amended) The process of Claim ~~[[8]]~~¹, wherein the sacrificial material comprises a metal, wherein the metal comprises aluminum.

10. (Original) The process of Claim 9, wherein selectively removing the sacrificial material comprises etching the metal with chlorine gas.

11. (Currently Amended) The process of Claim ~~[[8]]~~¹, wherein the sacrificial material comprises a metal, wherein the metal comprises nickel.

12. (Original) The process of Claim 11, wherein selectively removing the sacrificial material comprises etching the metal with carbon monoxide gas.

13. (Canceled).

14. (Currently Amended) The process of Claim ~~13~~¹, wherein the sacrificial material comprises an organic material, wherein the organic material comprises a photoresist.

15. (Original) The process of Claim 14, wherein selectively removing the sacrificial material comprises stripping away the sacrificial material by wet ashing.

16. (Original) The process of Claim 15, wherein stripping away the sacrificial material by wet ashing comprises reacting the sacrificial material with a sulfuric acid and hydrogen peroxide solution.

17. (Original) The process of Claim 14, wherein selectively removing the sacrificial material comprises stripping away the sacrificial material by dry ashing.

18. (Original) The process of Claim 17, wherein stripping away the sacrificial material by dry ashing comprises reacting the sacrificial material with an ozone or an oxygen plasma.

19. (Currently Amended) ~~The process of Claim 1,~~ A process for forming a conductive element, comprising:

providing a semiconductor substrate;

depositing a sacrificial material over the substrate, wherein the sacrificial material comprises a material that can be sublimed below about 400°C;